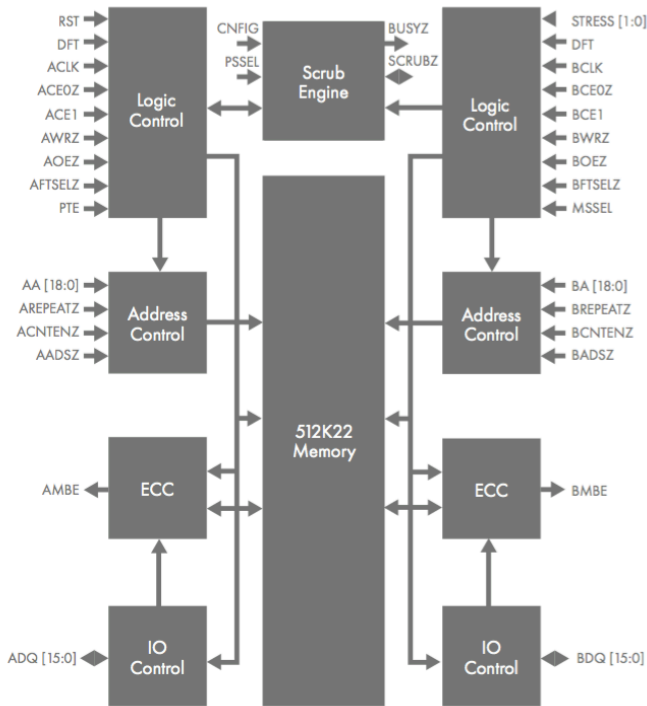


Radiation Hardened 8Mb Synchronous Dual-Port SRAM HS512K16



High density 8Mb Synchronous Dual-Port SRAM manufactured with HARDSIL® technology featuring extremely low operational and standby power, latch-up immunity and on-chip EDAC.



KEY FEATURES

- Manufactured with HARDSIL® technology
- Operates as a true dual-port synchronous 8Mbit SRAM memory (512K x 16) or standard single-port 8Mbit SRAM or flexible interconnect for multi-processor environments
- Functionally compatible with commercial 512K x 16 dual-port SRAM devices
- Operating voltages
 - Core 1.5V, IO 3.3V
- Selectable pipeline and Flow-Through modes
 - Clock cycle time <20nS Flow-Through, <15nS Pipeline mode
 - Access time <17nS Flow-Through, <12nS Pipeline mode
- Internal Error detection and correction (EDAC)
 - Single bit error detection and correction on read access
 - Optional background scrubbing
- Optional parity generation / checking
- Ultra low standby current <70mA typical @ 175C
- High temperature performance >1000 hour operating life at 200C
- Package
 - 128 pin ceramic QFP
 - Die available

RADIATION HARDENED PERFORMANCE

- TID > 300K rad (Si)
- Soft Error Rate (SER) with EDAC enabled < 1e-10 errors / bit-day
- Latch-up immunity > LET = 110 MeV-cm² / mg (T=125C)

APPLICATIONS

- Industrial
- Aerospace
- Medical
- Space
- Military

For more information, contact below or visit our web site at www.voragotech.com
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